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INTEGRATED CIRCUITS, SILICON MONOLITHIC,

BIPOLAR LOW POWER SCHOTTKY

QUADRUPLE 2-INPUT MULTIPLEXER

WITH STORAGE,

BASED ON TYPE 54LS398

ESCC Detail Specification No. 9408/015

ISSUE 1 October 2002



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space components coordination group

	Date	Approved by		
lssue/Rev.		SCCG Chairman	ESA Director General or his Deputy	
Issue 2	January 1994	Tommer's	talert	
Revision 'A'	February 1995	Tommen's	Hom	
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Rev. 'A'

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DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
			es Issue 1 and incorporates all modifications defined in	
			to Issue 1 and the following DCR's:-	
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		Table 1(a)	: Lead Material and/or Finish amended for existing Variants	22001
			: Variant 02 added and existing figure reference amended	22920
			: Variants 11 and 12 added	22881
		Table 1(b)	: No. 2, in Remarks, Note No. amended to "1"	23573
			: No. 3, in Remarks, Note No. amended to "2"	23573
			: No. 6, existing temperature specified for DIL/FP and Note No. amended to "3"	23573
			, new temperature and Note reference added for CCP	23573
ļ			: Note 1 renumbered as "2"	23573
1			: Note 2 renumbered as "3" and text amended	23573
			: Note 3 renumbered as "1"	23573
			: New Note 4 added	23573
		Figure 2(a)	: New figure added	22920
		Figure 2(b)	: Drawing and Table amended	23592
		Figure 2(c)	: New figure added : Title of the notes amended	22881 22881
		Notes to Figures	: Existing Notes deleted, new Notes added	22881
			: Note 2, "Not applicable" deleted, new Note added	22920
		Para. 4.2.2	: Deviation deleted, "None" added	21048
		Para. 4.2.4	: Deviation deleted, "None" added	22919
		Para. 4.2.5	: Deviation deleted, "None" added	22919
		Para. 4.3.2	: Paragraph rewritten	22920/
				23460
		Para. 4.4.2	: Paragraph rewritten	22881/
				22920
		Para. 4.5.2	: Paragraph rewritten	22881/
				22920
		Para. 4.5.3	: Paragraph standardised	23519
		Para. 4.6.3	: "and functional test sequence" deleted	23519
		Para. 4.7.1 Paras. 4.7.2 & 4.7.3	 "T_{amb}" added before " + 22 ± 3°C" In title and paragraph, "burn-in" amended to read "power burn-in" 	23519 23519
		Table 2, 3	: No. 62, in Test Conditions, pin no. changed to "20"	23633
1		Figure 4(h)	: In Note 1, t _o corrected to "0.5"	23633
		Para. 4.8	: Title amended	23573
		Table 6	: Changed order of V _{OL} and V _{OH}	23633
'A'	Feb. '95	P1. Cover Page		None
	160, 30	P2. DCN		None
		P14. Para. 4.3.2	: Maximum weights amended	221047
		1 14. 1 ala. 4.3.2	. maximum weignis amenueu	221041
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ISSUE 2

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APPENDICES (Applicable to specific Manufacturers only)'A'Agreed Deviations for Texas Instruments (F)

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1. <u>GENERAL</u>

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, low power bipolar Schottky Quadruple 2-Input Multiplexer with Storage, based on Type 54LS398. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 TRUTH TABLE

As per Figure 3(b).

- 1.8 <u>CIRCUIT SCHEMATIC</u> As per Figure 3(c).
- 1.9 <u>FUNCTIONAL DIAGRAM</u>

As per Figure 3(d).



.

TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
02	FLAT	2(a)	G4
05	DIL	2(b)	D7
06	DIL	2(b)	G4
11	CCP	2(c)	7
12	CCP	2(c)	4

TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Supply Voltage	V _{CC}	– 0.5 to 7.0	V	-
2	Input Voltage	V _{IN}	– 0.5 to 7.0	V	Note 1
3	Device Dissipation	PD	71.5	mWdc	Note 2
4	Operating Temperature Range	Т _{ор}	– 55 to + 125	°C	-
5	Storage Temperature Range	T _{stg}	– 65 to + 150	°C	-
6	Soldering Temperature For FP and DIP For CCP	T _{sol}	+ 265 + 245	°C	Note 3 Note 4

NOTES

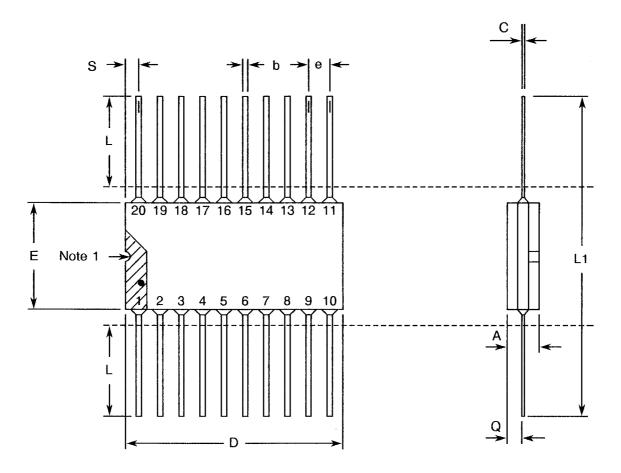
- 1. Input current limited to 18mA.
- 2. Must withstand added P_D due to short circuit conditions (i.e. I_{OS}) at one output for 5 seconds.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.



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FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE

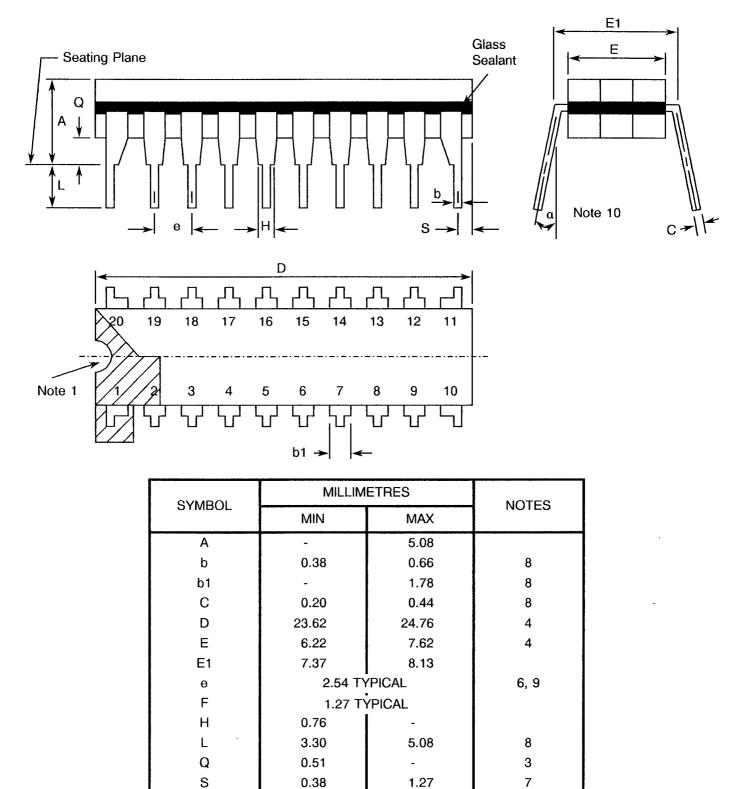


SYMBOL	MILLIM	NOTEO	
	MIN	MAX	NOTES
A	1.14	2.34	
b	0.38	0.56	8
С	0.08	0.23	8
D	-	12.95	4
Е	6.60	7.65	
E1	8.15	TYPICAL	4
e	1.27	TYPICAL	5, 9
L	6.35	9.40	8
L1	18.90	25.90	
Q	0.25	1.02	2
S	0.13	1.14	7



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - DUAL-IN-LINE PACKAGE



1.27

10

- ----

15°

S

α

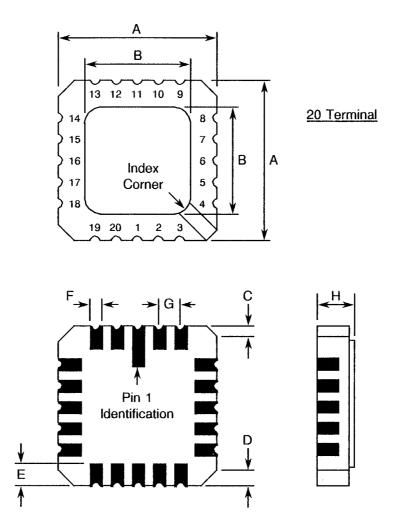
0°



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FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)



SYMBOL	MILLIM	NOTES	
	MIN.	MAX.	NUTES
A	8.687 9.093		-
В	7.798	9.093	-
С	0.250	0.510	11
D	0.889	1.143	12
E	1.140	1.400	8
F	0.559	0.712	8
G	1.27 TYPICAL		5, 9
Н	1.630 2.540		-

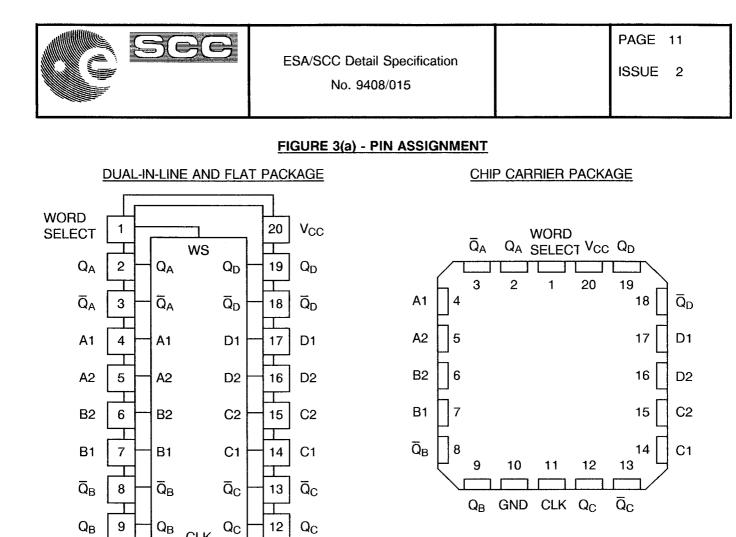




FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES TO FIGURES 2(a) TO 2(c)

- 1. Index area: a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages, the index shall be as shown in Figure 2(c).
- 2. Dimension Q shall be measured at the point of exit of the lead from the body.
- 3. Dimension Q shall be measured from the seating plane to the base plane.
- 4. This dimension allows for off-centre lids, meniscus and glass overrun.
- 5. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within ± 0.13mm of its true longitudinal position relative to Pins 1 and 20.
- 6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ± 0.25mm of its true longitudinal position relative to Pins 1 and 20.
- 7. Applies to all four corners.
- 8. All leads or terminals.
- 18 spaces for flat and dual-in-line packages.
 16 spaces for chip carrier packages.
- 10. Lead centre when α is 0°.
- 11. Index corner only 2 dimensions.
- 12. 3 non-index corners 6 dimensions.



(TOP VIEW)

CLK

11

CLK

FIGURE 3(b) - TRUTH TABLE

INPUTS		OUTPUTS			
WORD SELECT	CLOCK	Q _A	Q _B	Q _C	Q _D
L	↑	a1	b1	c1	d1
н	↑	a2	b2	c2	d2
х	L	Q _{A0}	Q _{B0}	Q _{C0}	Q _{D0}

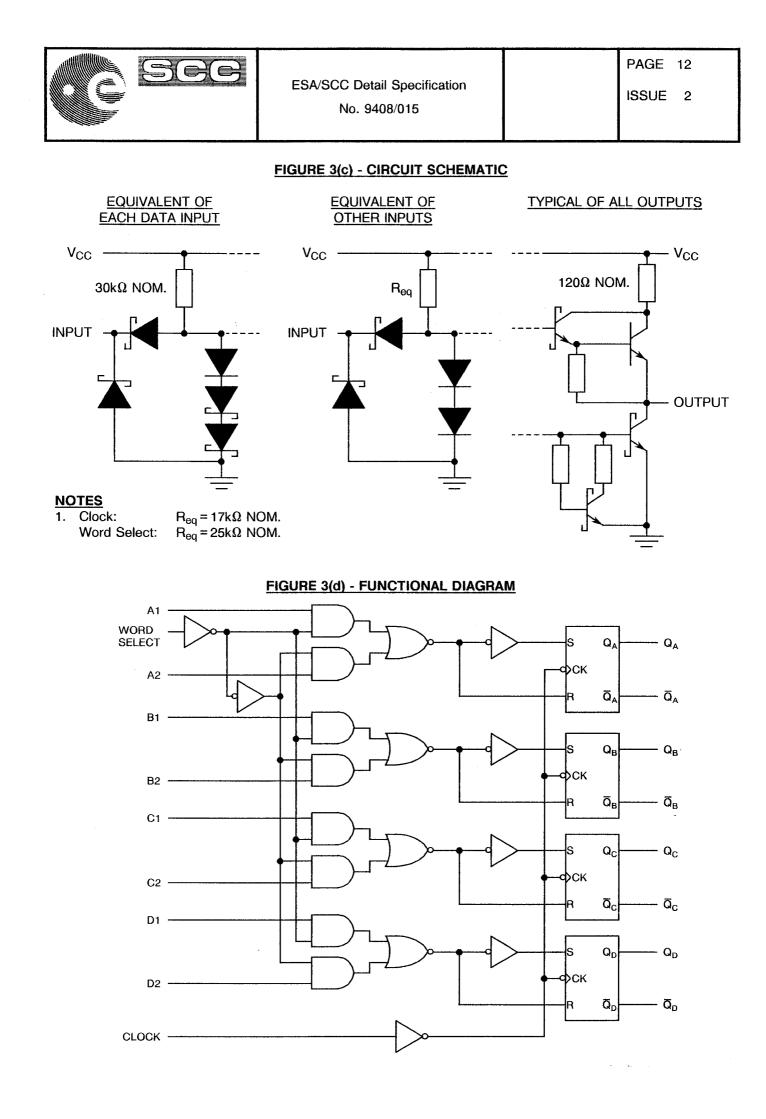
NOTES

GND

10

1. Logic Level Definitions: L=Low Level (Steady State), H=High Level (Steady State), ↑ = Transition from Low to High Level.

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2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:-

V_{IC} = Input Clamp Voltage. I_{CC} = Supply Current. V_{CC} = Supply Voltage.

4. **REQUIREMENTS**

4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

- 4.2.1 <u>Deviations from Special In-process Controls</u> None.
- 4.2.2 Deviations from Final Production Tests (Chart II) None.
- 4.2.3 Deviations from Burn-in Tests (Chart III)
 - (a) Para. 7.1.1(a), High Temperature Reverse Bias tests and subsequent electrical measurements related to this test shall be omitted.
 - (b) Para. 9.9.2, Electrical Measurements at High and Low Temperatures: Only a test result summary, based on go-no-go tests and presented in histogram form is required.
- 4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u> None.
- 4.2.5 <u>Deviations from Lot Acceptance Tests (Chart V)</u> None.



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Rev. 'A'

4.3 MECHANICAL REQUIREMENTS

4.3.1 <u>Dimension Check</u>

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.9 grammes for the flat package, 3.2 grammes for the dual-in-line package and 0.6 grammes for the chip carrier package.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be either Type 'D' or Type 'G' with either Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(c).



4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>940801505</u> B	
Detail Specification Number		
Type Variant (see Table 1(a)) ·		
Testing Level (B or C, as applic	cable)	

4.5.4 <u>Traceability Information</u>

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at T_{amb} = +22 ±3 °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at T_{amb} = +125 and -55 °C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Power Burn-in

Circuits for use in performing the power burn-in tests are shown in Figure 5 of this specification.

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TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS	LIM	ITS	UNIT
NO.	MIL-STD FIG. (PINS UNDER TEST) 883		(PINS UNDER TEST)	MIN	MAX	UNIT		
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 10	Input Current High Level 1	l _{iH1}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 2.7V (Pins 1-4-5-6-7-14-15-16- 17)	-	20	μА
11 to 19	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins 1-4-5-6-7-14-15-16- 17)	-	100	μА
20 to 28	Input Clamp Voltage	V _{IC}	3008	4(b)	V _{CC} = 4.5V, I _{IN} =18mA Note 2 (Pins 1-4-5-6-7-14-15-16- 17)	-	- 1.5	V
29 to 37	Input Current Low Level	Ι _{ΙL}	3009	4(c)	V _{CC} = 5.5V, V _{IN} = 0.4V (Pins 1-4-5-6-7-14-15-16- 17)	-	- 400	μA
38 to 45	Output Voltage Low Level	V _{OL}	3007	4(d)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OL} = 4.0mA$ (Pins 2-3-8-9-12-13-18-19)	-	0.4	V
46 to 53	Output Voltage High Level	V _{OH}	3006	4(e)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OH} = -400\mu A$ (Pins 2-3-8-9-12-13-18-19)	2.5	-	V
54 to 61	Short Circuit Output Current	los	3011	4(f)	V _{CC} = 5.5V Note 3 (Pins 2-3-8-9-12-13-18-19)	-20	- 100	mA
62	Supply Current	Icc	3005	4(g)	V _{CC} = 5.5V Note 5 (Pin 20)	-	13	mA

NOTES: See Page 17.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST)	LIM	ITS	UNIT
NO.	CHARACTERISTICS	STIVIBOL	MIL-STD FIG. 883		(NOTE 4)	MIN	MAX	
63 to 70	Propagation Delay, Low to High Level, Clock to Q and Q	t₽LH	3003	4(h)	$V_{CC} = 5.0V$ $R_{L} = 2.0k\Omega$ $C_{L} = 15pF$ <u>Pins</u> 11 to 2 11 to 3 11 to 8 11 to 9 11 to 12 11 to 13 11 to 18 11 to 18 11 to 19		27	ns
71 to 78	Propagation Delay, High to Low Level, Clock to Q and Q	t₽HL	3003	4(h)	$V_{CC} = 5.0V$ $R_L = 2.0k\Omega$ $C_L = 15pF$ <u>Pins</u> 11 to 2 11 to 3 11 to 8 11 to 9 11 to 12 11 to 13 11 to 18 11 to 19	-	32	ns

NOTES

- 1. Go-no-go test with V_{IL} = 0.3V; V_{IH} = 3.0V; trip point 1.5V.
- 2. All inputs and outputs not under test shall be open.
- 3. No more than one output should be shorted at a time, and only for 1 second maximum. I_{OS} measurement may be performed with $V_{OUT} = 2.25V$ instead of 0V. In this case, the limits are divided by 2.
- 4. Propagation delay measurements shall be performed as a go-no-go test on a 100% basis. Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III Burn-in Test.
- 5. All outputs open and all inputs, except clock, low.

I_{CC} is measured after applying a single pulse of 4.5V to Ground to the clock input.



TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES,+ 125(+0-5) °C AND - 55(+5-0) °C

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS	LIM	IITS	UNIT
INO.	CHARACTERISTICS	MIL-STD FIG. (PINS UNDER TEST) 883		MIN	МАХ			
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 10	Input Current High Level 1	l _{IH1}	3010	4(a)	4(a) $V_{CC} = 5.5V, V_{IN} = 2.7V$ (Pins 1-4-5-6-7-14-15-16- 17)		20	μA
11 to 19	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins 1-4-5-6-7-14-15-16- 17)	-	100	μA
20 to 28	Input Clamp Voltage	V _{IC}	3008	4(b)	V _{CC} = 4.5V, I _{IN} =18mA Note 2 (Pins 1-4-5-6-7-14-15-16- 17)	-	- 1.5	V
29 to 37	Input Current Low Level	Ι _{ΙL}	3009	4(c)	V _{CC} = 5.5V, V _{IN} = 0.4V (Pins 1-4-5-6-7-14-15-16- 17)	-	-400	μA
38 to 45	Output Voltage Low Level	V _{OL}	3007	4(d)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OL} = 4.0mA$ (Pins 2-3-8-9-12-13-18-19)	-	0.4	V
46 to 53	Output Voltage High Level	V _{OH}	3006	4(e)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OH} = -400\mu A$ (Pins 2-3-8-9-12-13-18-19)	2.5	-	V
54 to 61	Short Circuit Output Current	los	3011	4(f)	V _{CC} = 5.5V Note 3 (Pins 2-3-8-9-12-13-18-19)	-20	- 100	mA
62	Supply Current	lcc	3005	4(g)	V _{CC} = 5.5V Note 5 (Pin 20)	-	13	mA

NOTES: See Page 17.

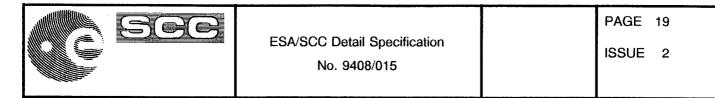
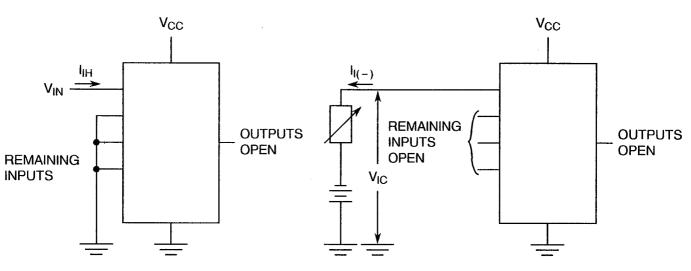


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - HIGH LEVEL INPUT CURRENT

FIGURE 4(b) - INPUT CLAMP VOLTAGE



NOTES

1. Each input to be tested separately.

NOTES 1. Each input to be

1. Each input to be tested separately.

FIGURE 4(c) - LOW LEVEL INPUT CURRENT

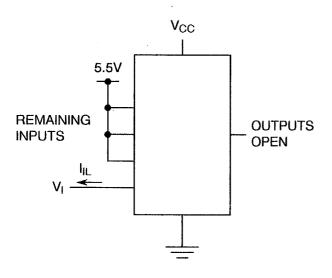
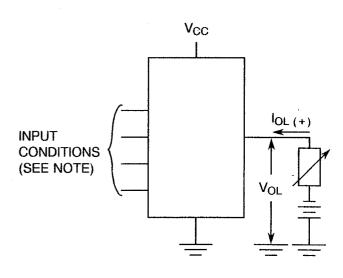


FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE



NOTES

1. Each input to be tested separately.

NOTES

1. Test per Truth Table.

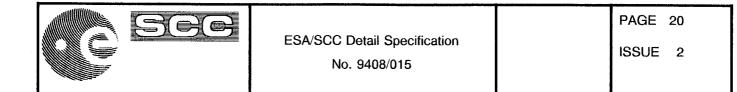
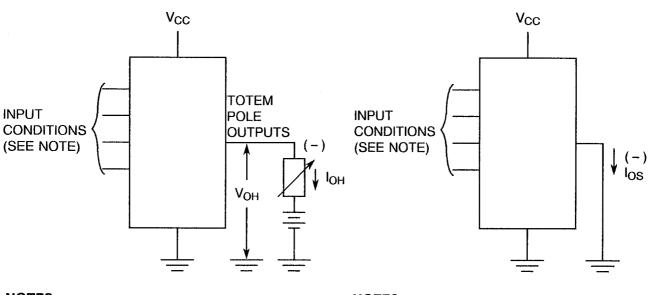


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE

FIGURE 4(f) - SHORT CIRCUIT OUTPUT CURRENT

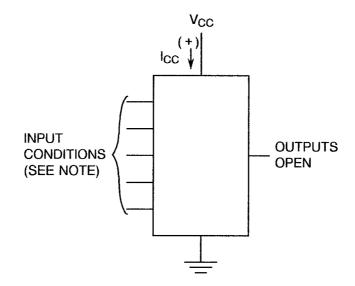


NOTES

1. Test per Truth Table.

NOTES 1. Test per Truth Table.

FIGURE 4(g) - SUPPLY CURRENT

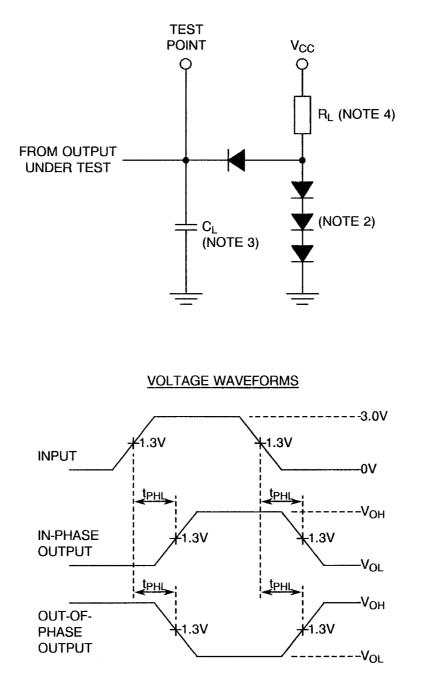


NOTES

1. See Note 5 to Table 2.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(h) - DYNAMIC TEST AND SWITCHING WAVEFORMS



NOTES

- 1. The generator has the following characteristics: $V_{GEN} = 3.0 \pm 0.2V$, $t_r < 15$ ns, $t_f < 6.0$ ns, $t_p = 0.5$ µs, PRR = 1.0MHz, $Z_{OUT} = 50\Omega$.
- 2. All diodes are 1N916 or 1N3064.

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- 3. C_L = 15pF minimum, including scope probe, wiring and stray capacitance without package in test fixture.
- 4. $R_L = 2.0 k\Omega \pm 5\%$.



TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2 to 10	Input Current High Level 1	l _{IH1}	As per Table 2	As per Table 2	±20 or (1) ±0.5	% µА
29 to 37	Input Current Low Level	l _{IL}	As per Table 2	As per Table 2	±18	μА
38 to 45	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	±60	mV
46 to 53	Output Voltage High Level	V _{OH}	As per Table 2	As per Table 2	± 240	mV

NOTES

1. Whichever is greater, referred to the initial value.

TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T _{amb}	+ 125(+ 0 – 5)	°C
2	Power Supply Voltage	V _{CC}	5(+ 0.5 – 0)	V
3	Pulse Voltage	V _{GEN}	0.5 max. to 3.0 min.	V
4	Frequency	f	100 (Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	t _r	50 max.	μs
7	Fall Time	t _f	50 max.	μs
8	Duty Cycle	-	20 min.	%

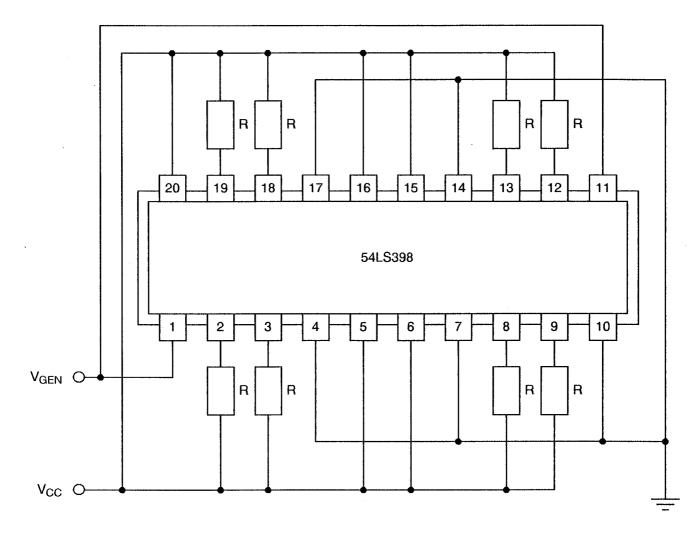
NOTES

1. Tolerance ±10%.



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FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST



<u>NOTES</u> 1. R=1.2kΩ.



4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> <u>SPECIFICATION NO. 9000)</u>

4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22±3 °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 <u>Electrical Measurements on Completion of Endurance Tests</u>

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ °C}$.

4.8.4 <u>Conditions for Operating Life Tests</u>

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 <u>Electrical Circuits for Operating Life Tests</u>

Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 <u>Conditions for High Temperature Storage Test</u>

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be T_{amb} = +150(+0-5) °C.



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TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST	CHAN	UNIT	
NO.		STMDUL	TEST METHOD	CONDITIONS	(Δ)	ABSOLUTE	UNIT
2 to 10	Input Current High Level 1	[‡] IH1	As per Table 2	As per Table 2	±0.5	-	μА
11 to 19	Input Current High Level 2	I _{IH2}	As per Table 2	As per Table 2	-	100	μА
29 to 37	Input Current Low Level	l _{IL}	As per Table 2	As per Table 2	±16	-	μА
38 to 45	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	± 60	-	mV
46 to 53	Output Voltage High Level	V _{OH}	As per Table 2	As per Table 2	± 240	-	mV
62	Supply Current	lcc	As per Table 2	As per Table 2	± 20	-	%



APPENDIX 'A'

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AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 4.2.1	Scanning Electron Microscope (SEM) Inspection may be performed using TIF document TIF 3.61.610.001.
Para. 4.2.2	Prior to Die Shear Test TIF may perform a Radiographic Inspection on the randomly chosen samples to be subjected to this test, using TIF document TIF 50.42-3002.
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TIF 50.42-3002.